

TSM2301

20V P-Channel MOSFET



SOT-23

3 1 2

Pin Definition:

- 1. Gate
- 2. Source
- 3. Drain

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-20	130 @ V _{GS} = -4.5V	-2.8
	190 @ V _{GS} = -2.5V	-2.0

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

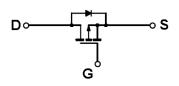
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing
TSM2301CX RF	SOT-23	3Kpcs / 7" Reel

Block Diagram



P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V_{DS}	-20	V	
Gate-Source Voltage		V_{GS}	±8	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	-2.8	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	-8	Α	
Continuous Source Current (Diode Condu	uction) ^{a,b}	I _S	-0.72	Α	
Maximum Power Dissipation	Ta = 25°C	Ъ	0.9	W	
	Ta = 75°C	─ P _D	0.57		
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T _L	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	120	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.
- c. Surface Mounted on FR4 Board,



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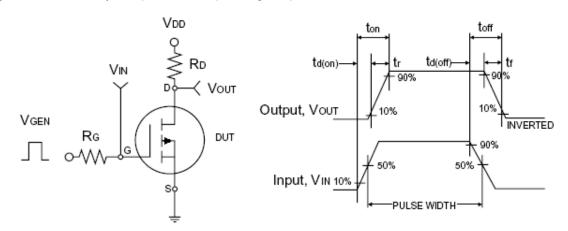


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static	Static					
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-0.45		-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -9.6V, V_{GS} = 0V$	I _{DSS}			-1.0	μA
On-State Drain Current ^a	$V_{DS} = -10V, V_{GS} = -5V$	I _{D(ON)}	-6			Α
Drain-Source On-State Resistance ^a	$V_{GS} = -4.5V$, $I_D = -2.8A$			85	130	
Dialii-Source Oil-State Resistance	$V_{GS} = -2.5V$, $I_{D} = -2.0A$	R _{DS(ON)}		122	190	mΩ
Forward Transconductance ^a	$V_{DS} = -5V, I_{D} = -4A$	g _{fs}		6.5		S
Diode Forward Voltage	$I_S = -0.75A$, $V_{GS} = 0V$	V_{SD}		- 0.8	-1.2	V
Dynamic ^b						
Total Gate Charge	$I_S = -0.75A$, $V_{GS} = 0V$ $V_{DS} = -6V$, $I_D = -2.8A$, $V_{GS} = -4.5V$	Q_g		5.4	10	nC
Gate-Source Charge		Q_gs		0.8		
Gate-Drain Charge	V _{GS} = -4.5 V	Q _{gd}		1.1		
Input Capacitance	.,	C _{iss}		447		
Output Capacitance	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	Coss		127		pF
Reverse Transfer Capacitance	1 - 1.0WINZ	C _{rss}		80		
Switching ^c						
Turn-On Delay Time	N 0 00	$t_{d(on)}$		5	25	
Turn-On Rise Time	$V_{DD} = -6V, R_L = 6\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	t _r		19	60	nC
Turn-Off Delay Time		$t_{d(off)}$		95	110	nS
Turn-Off Fall Time	116 022	t _f		65	80	

Notes:

- a. pulse test: PW =300 μ S, duty cycle =2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

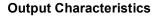


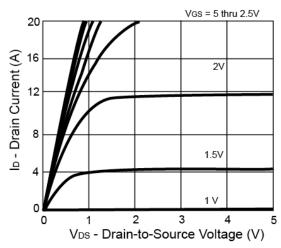




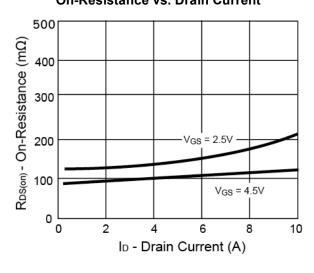


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

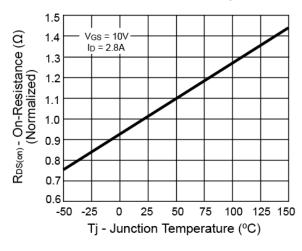




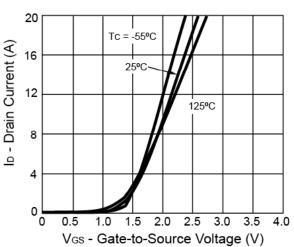
On-Resistance vs. Drain Current



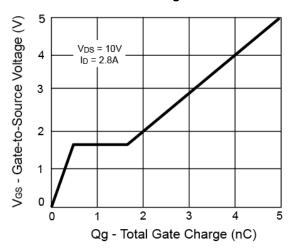
On-Resistance vs. Junction Temperature



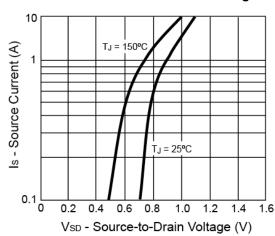
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





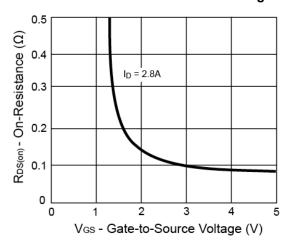


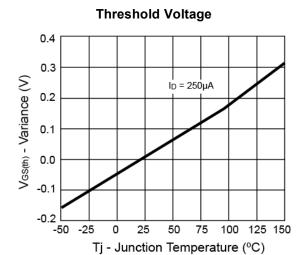




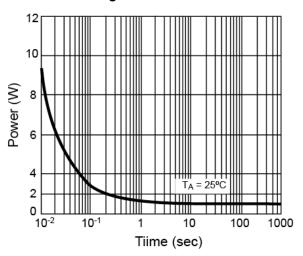
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

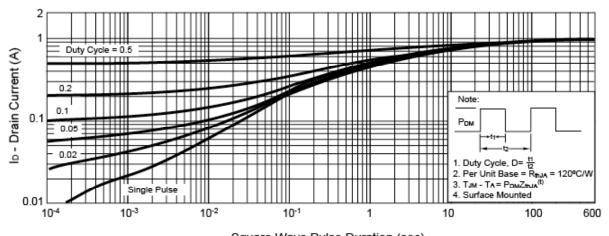




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



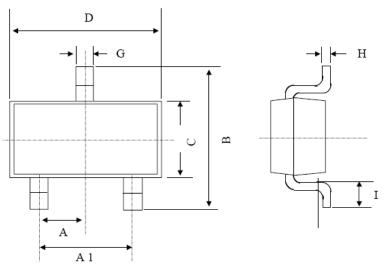
Square Wave Pulse Duration (sec)



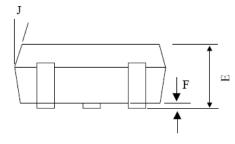




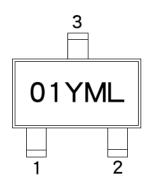
SOT-23 Mechanical Drawing



SOT-23 DIMENSION					
SUI-23 DIMENSION NILLIMETERS INCHES					
DIM					
	MIN	MAX	MIN	MAX.	
Α	0.95	BSC	0.037	BSC	
A1	1.9 I	BSC	0.074	BSC	
В	2.60	3.00	0.102	0.118	
С	1.40	1.70	0.055	0.067	
D	2.80	3.10	0.110	0.122	
Е	1.00	1.30	0.039	0.051	
F	0.00	0.10	0.000	0.004	
G	0.35	0.50	0.014	0.020	
Н	0.10	0.20	0.004	0.008	
I	0.30	0.60	0.012	0.024	
J	5°	10°	5°	10°	



Marking Diagram



01 = Device Code

Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



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